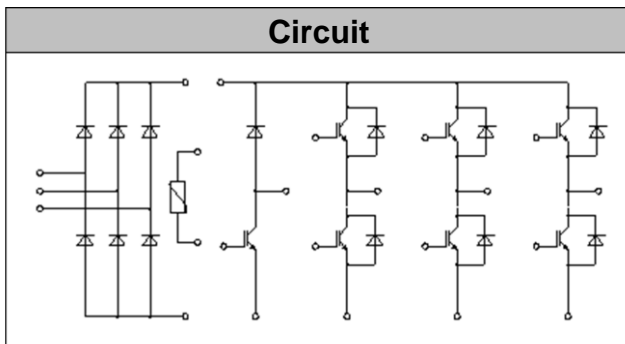


IGBT Modules

V _{CES}	1200V
I _C	15A

Applications

- Motor Drivers
- AC and DC Servo Drive Amplifier
- UPS (Uninterruptible Power Supplies)



Features

- Low switching losses
- Low V_{CE(sat)} with positive temperature coefficient
- Including fast & soft recovery anti-parallel FWD
- Low inductance case
- High short circuit capability(10us)
- Isolated heatsink using DBC technology
- Maximum junction temperature 175°C

● IGBT- inverter

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V _{CES}	V _{GE} =0V, I _C =1mA, T _{vj} =25°C	1200	V
Continuous Collector Current	I _C	T _C =100°C, T _{vjmax} =175°C	15	A
Repetitive Peak Collector Current	I _{CRM}	t _p =1ms	30	A
Gate-Emitter Voltage	V _{GES}	T _{vj} =25°C	±20	V
Total Power Dissipation	P _{tot}	T _C =25°C T _{vjmax} =175°C	165	W



● **IGBT- inverter**

Characteristic values

Parameter	Symbol	Conditions	Value			Unit	
			Min.	Typ.	Max.		
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=0.5mA, T_{vj}=25^{\circ}C$	5.2	5.8	6.4	V	
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=15A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.90		V	
		$I_C=15A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.10			
		$I_C=15A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.20			
Gate Charge	Q_G			0.15		uC	
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V, f=1MHz, T_{vj}=25^{\circ}C$		0.98		nF	
Reverse Transfer Capacitance	C_{res}			0.034		nF	
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA	
Turn-on Delay Time	$t_{d(on)}$	$I_C=15A, V_{CE}=600V, V_{GE}=\pm 15V, R_G=39\Omega, T_{vj}=25^{\circ}C$		63		ns	
Rise Time	t_r			31		ns	
Turn-off Delay Time	$t_{d(off)}$			87		ns	
Fall Time	t_f			305		ns	
Energy Dissipation During Turn-on Time	E_{on}			2.03		mJ	
Energy Dissipation During Turn-off Time	E_{off}			1.05		mJ	
Turn-on Delay Time	$t_{d(on)}$		$I_C=15A, V_{CE}=600V, V_{GE}=\pm 15V, R_G=39\Omega, T_{vj}=150^{\circ}C$		64		ns
Rise Time	t_r				35		ns
Turn-off Delay Time	$t_{d(off)}$				92		ns
Fall Time	t_f				324		ns
Energy Dissipation During Turn-on Time	E_{on}			2.23		mJ	
Energy Dissipation During Turn-off Time	E_{off}			1.19		mJ	
SC Data	I_{SC}	$t_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150^{\circ}C, V_{CC}=900V, V_{CEM} \leq 1200V$			55		A



● Diode-inverter

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}C$	1200	V
Continuous DC Forward Current	I_F		15	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1ms$	30	A
I^2t -value	I^2t	$V_R=0V, t_p=10ms, T_{vj}=125^{\circ}C$	16.0	A ² s
		$V_R=0V, t_p=10ms, T_{vj}=150^{\circ}C$	14.0	

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=15A, T_{vj}=25^{\circ}C$		2.00		V
		$I_F=15A, T_{vj}=125^{\circ}C$		1.80		
		$I_F=15A, T_{vj}=150^{\circ}C$		1.75		
Recovered Charge	Q_{rr}	$I_F=15A$		0.48		uC
Peak Reverse Recovery Current	I_{rr}	$V_R=600V$ $-di_F/dt=600A/us$		13		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=25^{\circ}C$		0.48		mJ
Recovered Charge	Q_{rr}	$I_F=15A$		0.62		uC
Peak Reverse Recovery Current	I_{rr}	$V_R=600V$ $-di_F/dt=600A/us$		14		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=150^{\circ}C$		0.7		mJ



● **IGBT-brake-chopper**
Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_C	$T_C=100^{\circ}C, T_{vjmax}=175^{\circ}C$	15	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	30	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_C=25^{\circ}C, T_{vjmax}=175^{\circ}C$	165	W

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=0.5mA, T_{vj}=25^{\circ}C$	5.2	5.8	6.4	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=15A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.90		V
		$I_C=15A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.10		
		$I_C=15A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.20		
Gate Charge	Q_G			0.15		uC
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V, f=1MHz, T_{vj}=25^{\circ}C$		0.98		nF
Reverse Transfer Capacitance	C_{res}			0.034		nF
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=15A, V_{CE}=600V, V_{GE}=\pm 15V, R_G=39\Omega, T_{vj}=25^{\circ}C$		63		ns
Rise Time	t_r			31		ns
Turn-off Delay Time	$t_{d(off)}$			87		ns
Fall Time	t_f			305		ns
Energy Dissipation During Turn-on Time	E_{on}			2.03		mJ
Energy Dissipation During Turn-off Time	E_{off}			1.05		mJ



Turn-on Delay Time	$t_{d(on)}$	$I_C=15A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=39\Omega$ $T_{vj}=150^\circ C$	64	ns
Rise Time	t_r		35	ns
Turn-off Delay Time	$t_{d(off)}$		92	ns
Fall Time	t_f		324	ns
Energy Dissipation During Turn-on Time	E_{on}		2.23	mJ
Energy Dissipation During Turn-off Time	E_{off}		1.19	mJ
SC Data	I_{SC}		$t_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150^\circ C,$ $V_{CC}=900V, V_{CEM} \leq 1200V$	55

● Diode-brake-chopper

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^\circ C$	1200	V
Continuous DC Forward Current	I_F		10	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1ms$	20	A
I^2t -value	I^2t	$V_R=0V, t_p=10ms, T_{vj}=125^\circ C$	16.0	A ² s
		$V_R=0V, t_p=10ms, T_{vj}=150^\circ C$	14.0	

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=10A, T_{vj}=25^\circ C$		2.00		V
		$I_F=10A, T_{vj}=125^\circ C$		1.85		
		$I_F=10A, T_{vj}=150^\circ C$		1.80		
Recovered Charge	Q_{rr}	$I_F=10A$		0.26		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600V$ $-di_F/dt=600A/\mu s$		11		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=25^\circ C$		0.28		mJ
Recovered Charge	Q_{rr}	$I_F=10A$		0.37		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600V$ $-di_F/dt=600A/\mu s$		12		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=150^\circ C$		0.65		mJ



● Diode-rectifier

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}C$	1600	V
Average output Current 50/60Hz, sine wave	$I_{F(AV)}$	$T_C=100^{\circ}C$	20	A
Maximum RMS Current at Rectifier Output	I_{RMSM}	$T_C=100^{\circ}C$	40	A
Surge Forward Current	I_{FSM}	$V_R=0V, t_p=10ms, T_{vj}=45^{\circ}C$	270	A
I^2t -value	I^2t	$V_R=0V, t_p=10ms, T_{vj}=45^{\circ}C$	360	A^2s

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	V_F	$I_F=15A, T_{vj}=150^{\circ}C$		0.96		V
Reverse Current	I_R	$T_{vj}=150^{\circ}C, V_R=1600V$			1.0	mA

● NTC-Thermistor

Characteristic Values

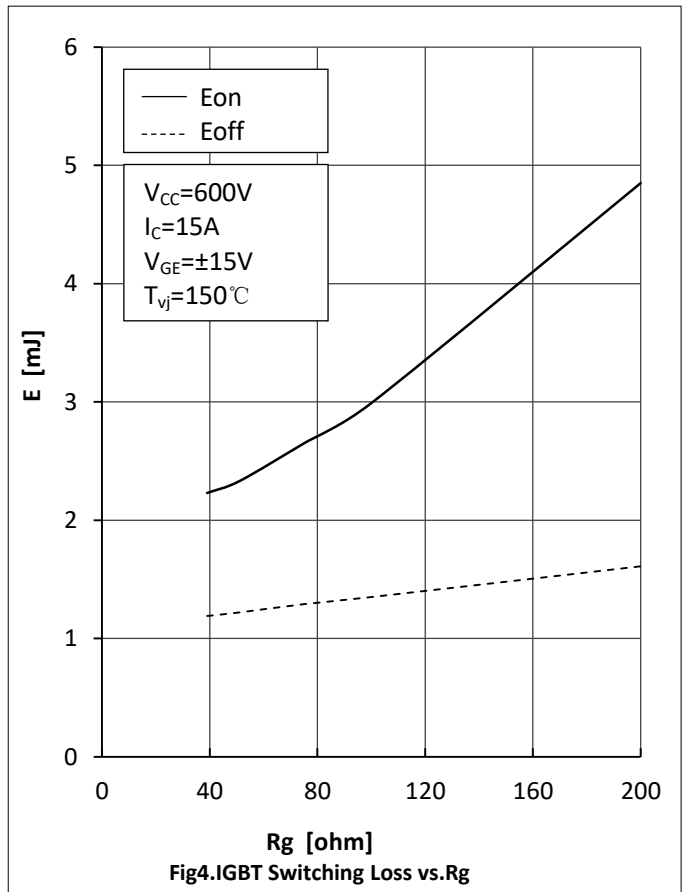
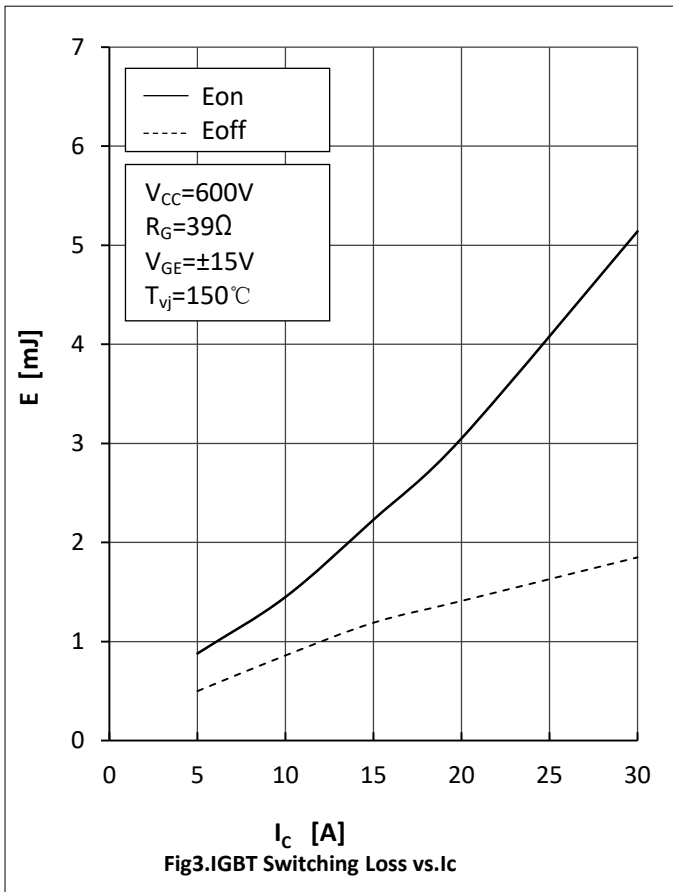
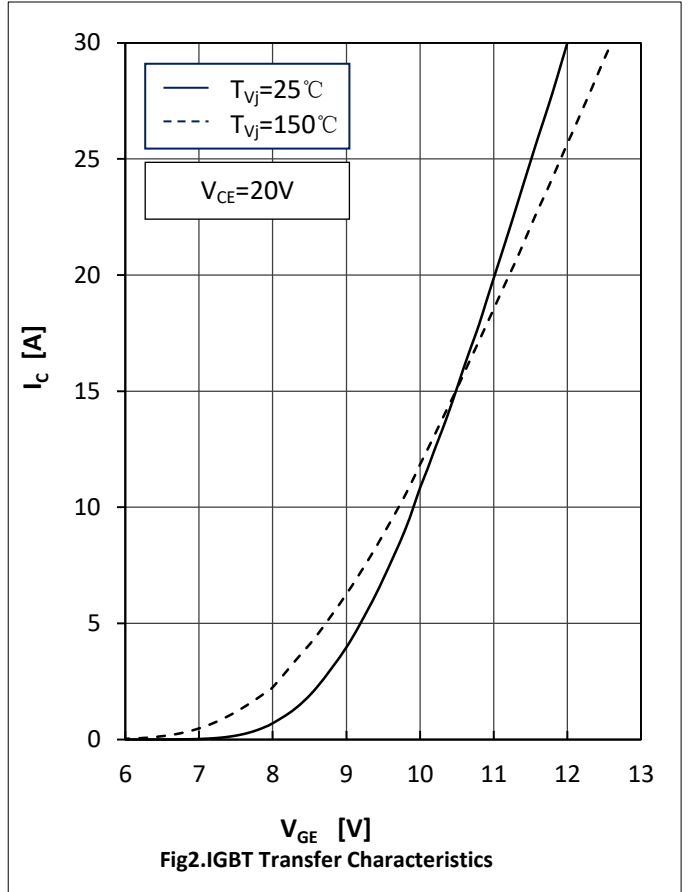
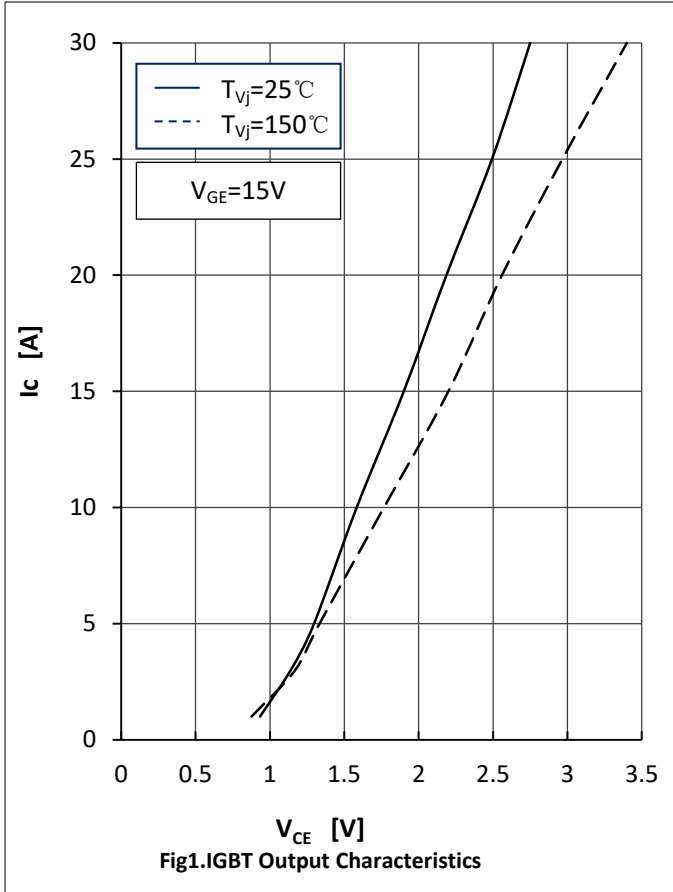
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Rated Resistance	R_{25}			5.0		k Ω
Deviation of R100	$\Delta R/R$	$T_C=100^{\circ}C, R_{100}=493.3\Omega$	-5		5	%
Power Dissipation	P_{25}				20.0	mW
B-value	$B_{25/50}$	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$		3375		K

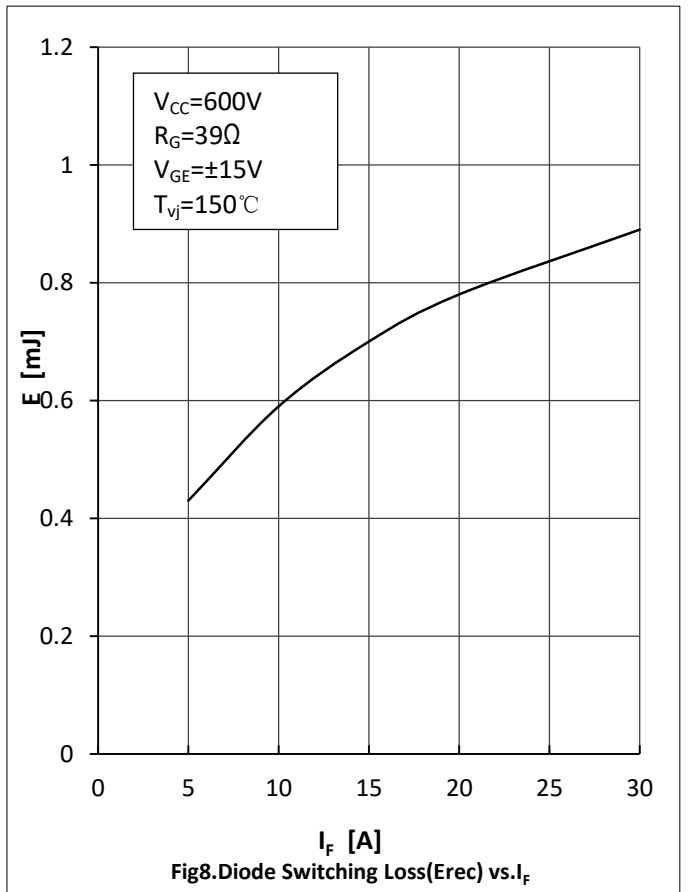
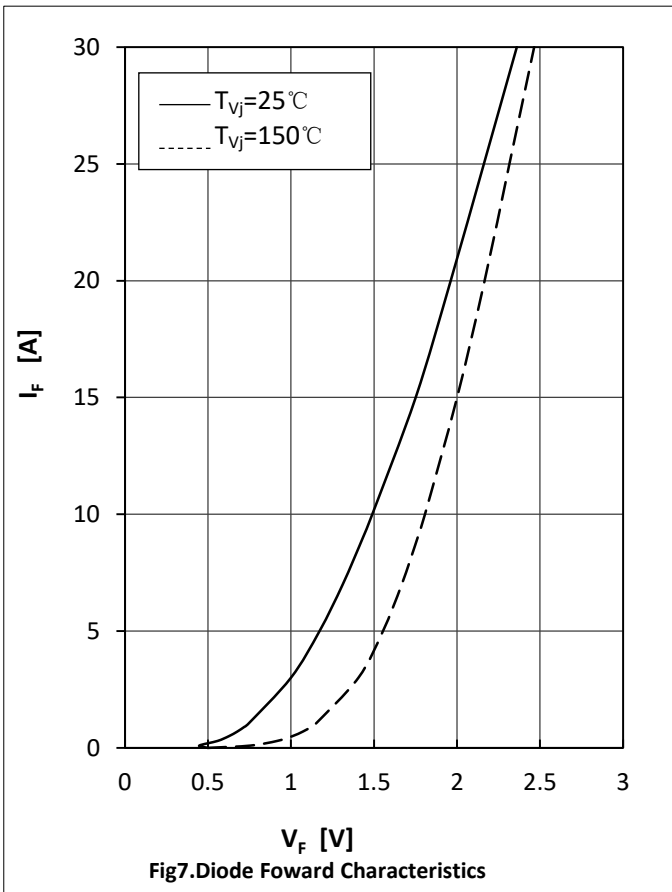
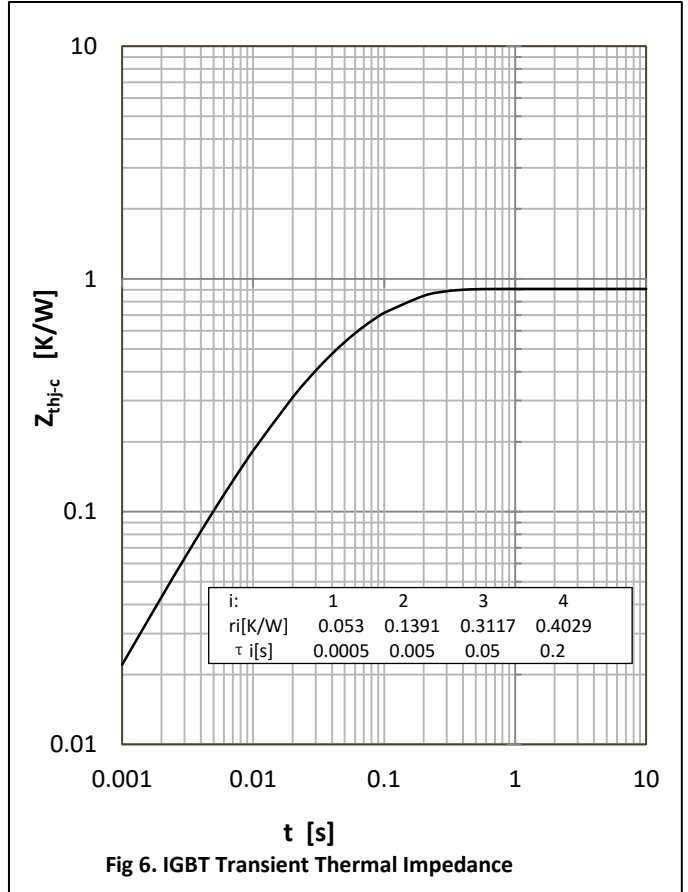
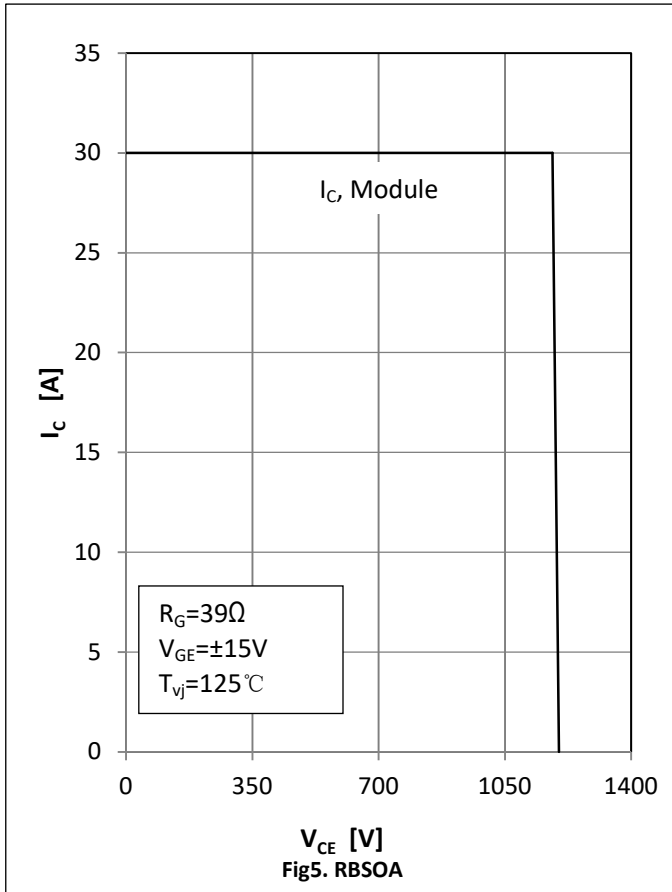


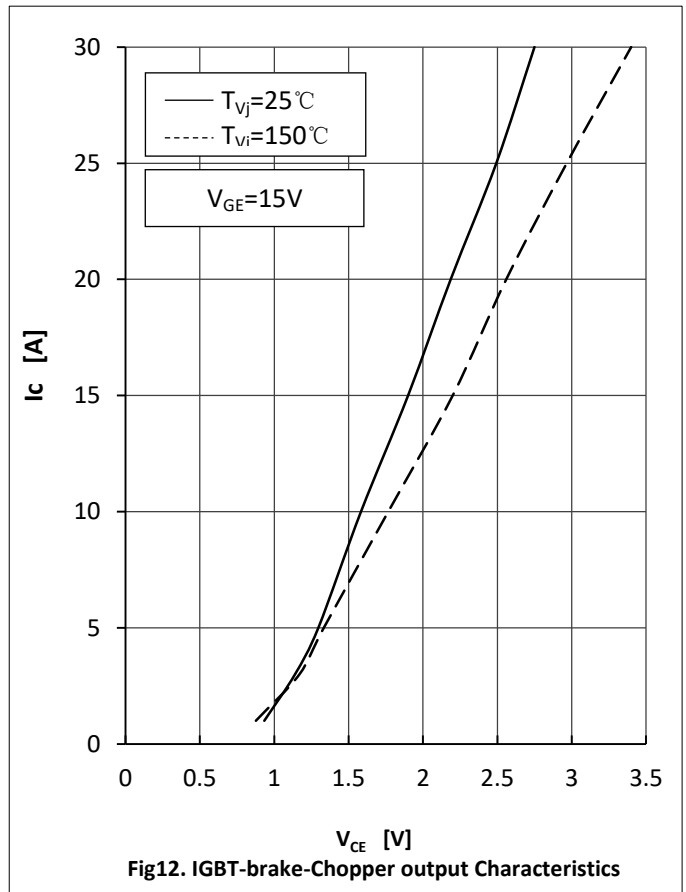
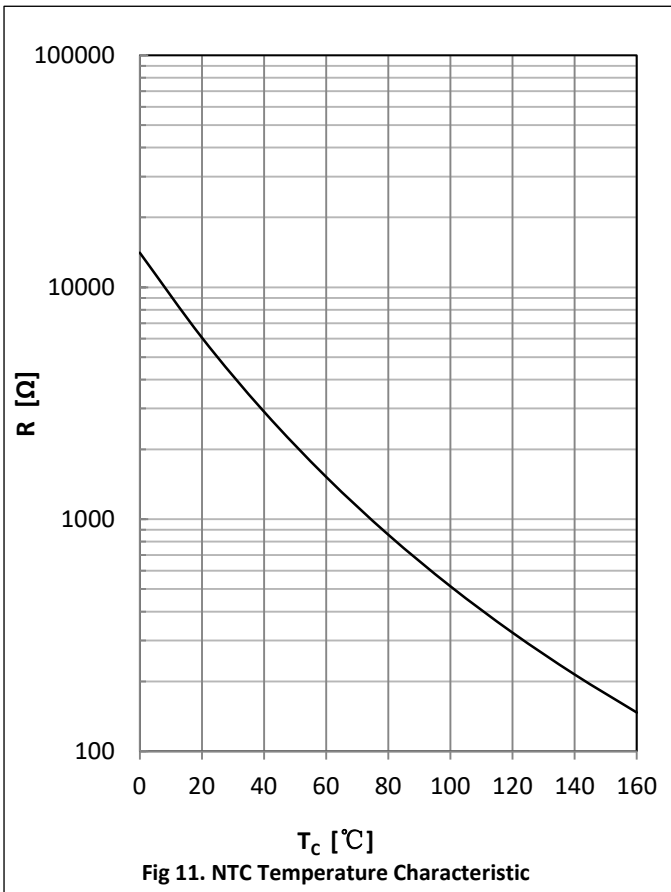
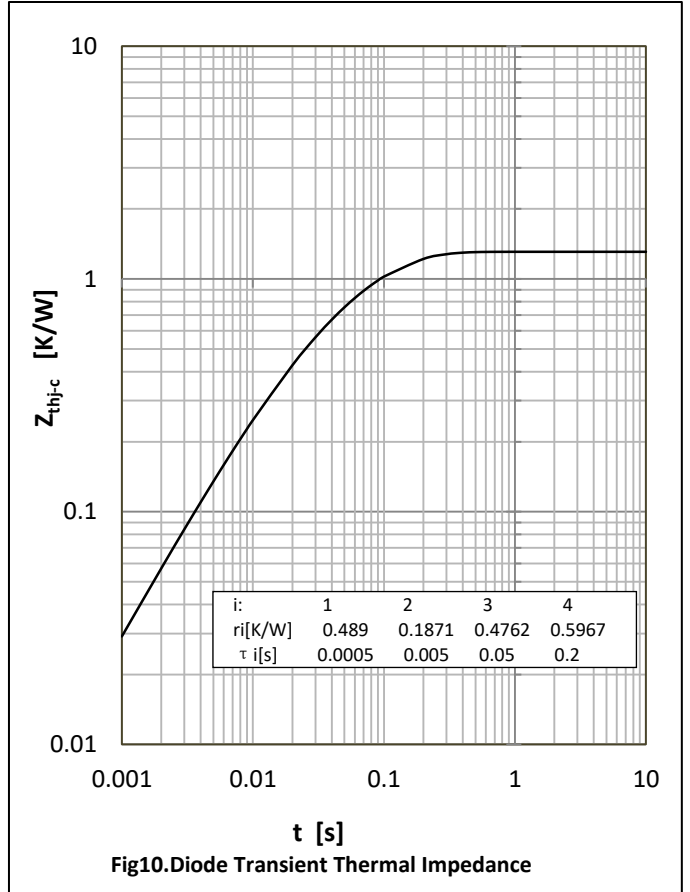
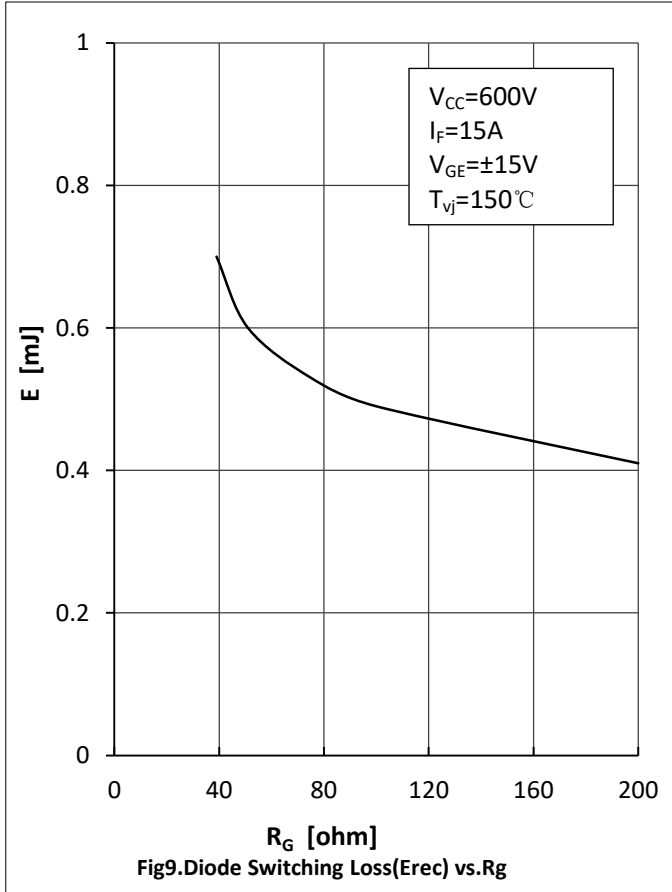
● Module Characteristics

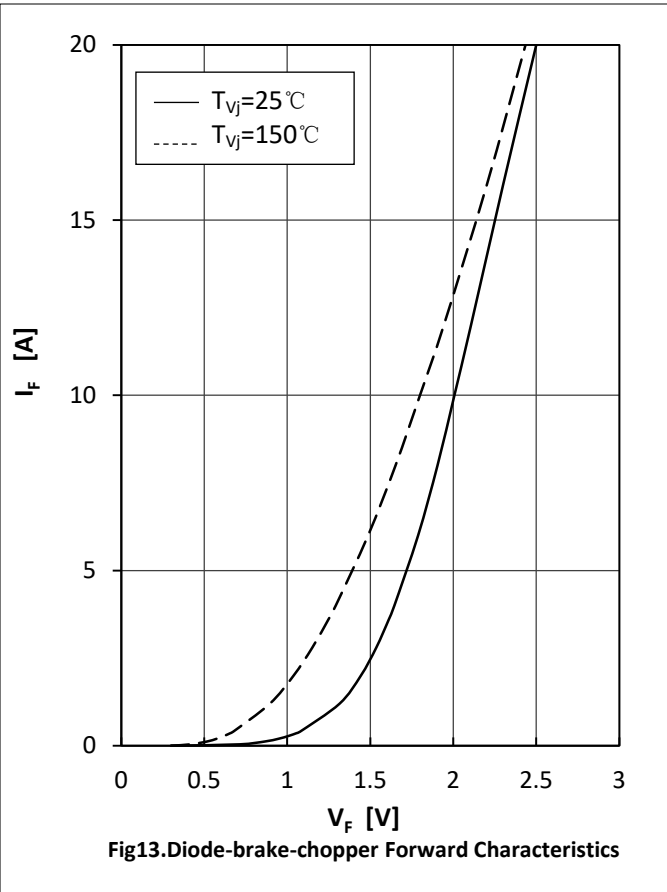
$T_C=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation Voltage	V_{isol}	$t=1\text{min}, f=50\text{Hz}$	2500			V
Maximum Junction Temperature	T_{jmax}				175	$^\circ\text{C}$
Operating Junction Temperature	$T_{\text{vj op}}$		-40		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-40		125	$^\circ\text{C}$
Stray-inductance-module	L_{SCE}			30		nH
Module lead resistance, terminals-chip	$R_{\text{CC}'+\text{EE}'}$	$T_C=25^\circ\text{C}$, per switch		5.00		m Ω
	$R_{\text{AA}'+\text{CC}'}$			6.00		
Thermal Resistance Junction-to Case	$R_{\theta\text{JC}}$	per IGBT-inverter		0.90		K/W
		per Diode-inverter		1.30		
		per IGBT-brake-chopper		0.90		
		per Diode-chopper		1.70		
		per Diode-rectifier		1.03		
Thermal Resistance Case-to Sink	$R_{\theta\text{CS}}$	per IGBT-inverter		0.95		K/W
		per Diode-inverter		1.05		
		per IGBT-brake-chopper		0.95		
		per Diode-chopper		1.30		
		per Diode-rectifier		1.17		
		per Module		0.037		
Mounting Force Per Clamp	F		30		80	N
Weight of Module	G			45		g



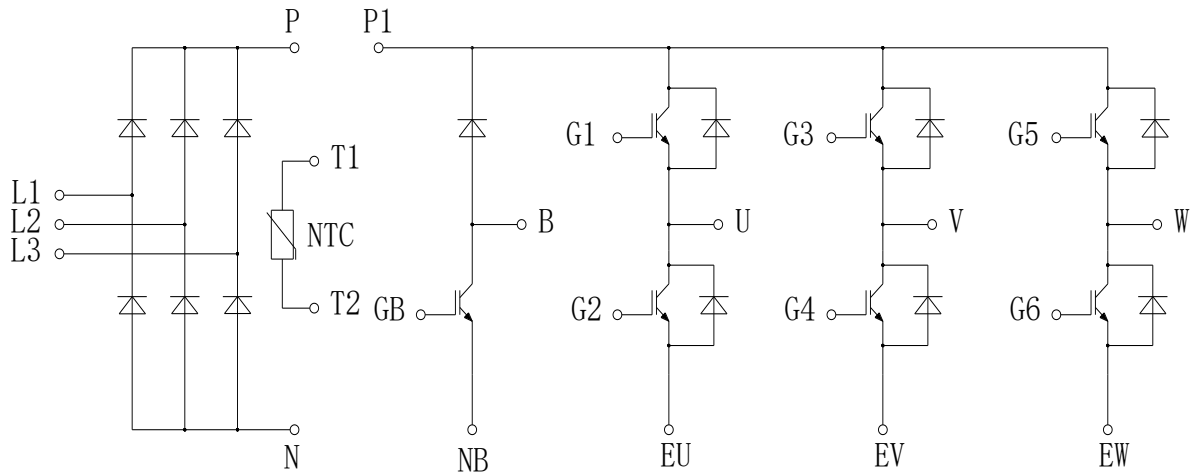




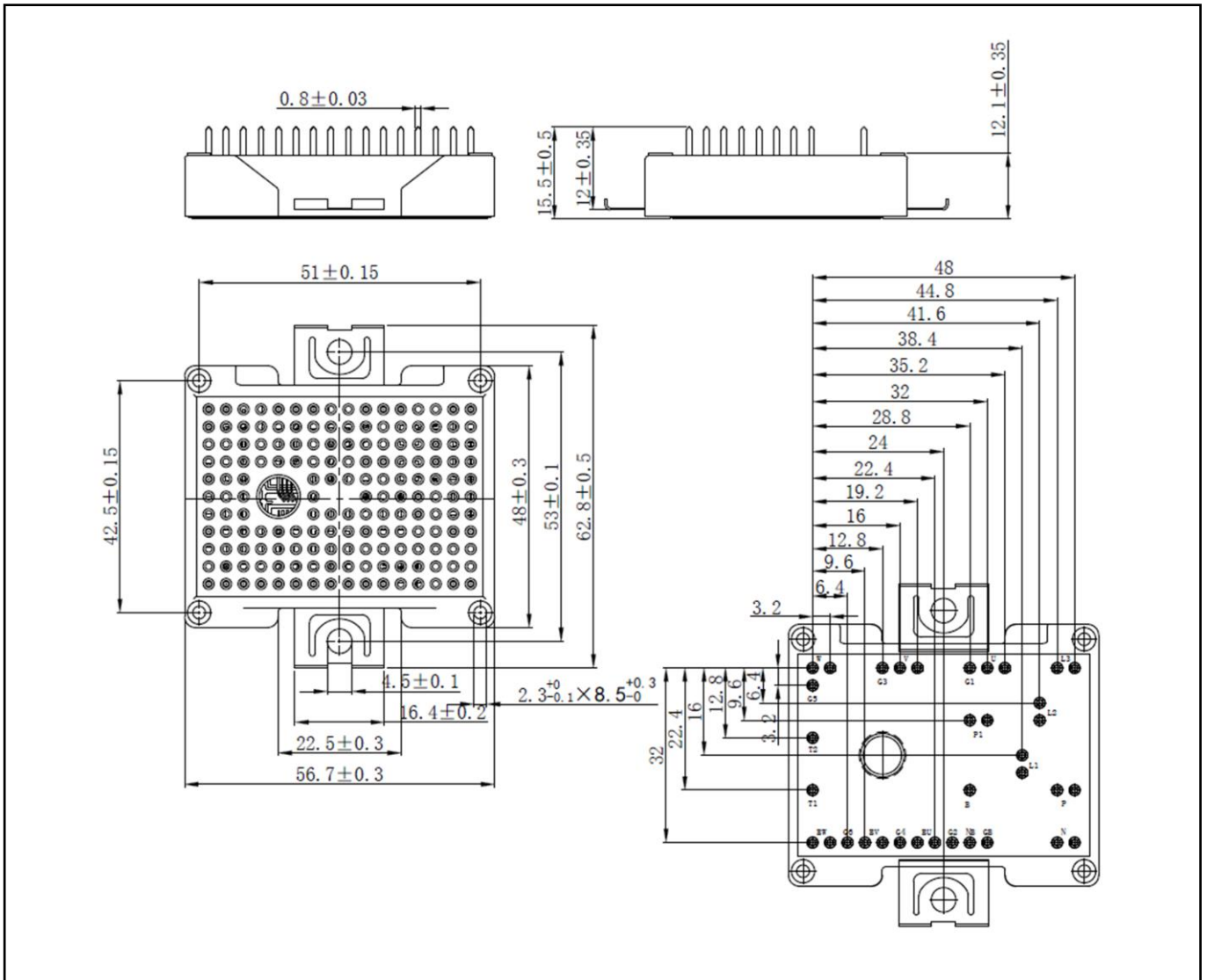




Circuit Diagram



Package Dimensions





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